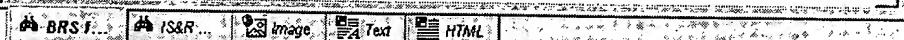


<input checked="" type="checkbox"/>	(0) ((float\$3 adj gate) same (control adj gate)) same (ald (at (31) ((float\$3 adj gate) same (control adj gate)) and (ald (at (76456) aluminum adj oxide
<input checked="" type="checkbox"/>	(15399) ((barrier near (height tunnel)) ((energy diagram) ne (10315) work adj function
<input checked="" type="checkbox"/>	(24895) ((barrier near (height tunnel)) ((energy diagram) ne (14) ((float\$3 adj gate) same (control adj gate)) same (alum (97) ((float\$3 adj gate) same (control adj gate)) same (((bar (0) ((float\$3 adj gate) same (control adj gate)) same (((bar (0) ((float\$3 adj gate) same (control adj gate)) same (((bar (173565) metal adj oxide
<input checked="" type="checkbox"/>	(10) ((float\$3 adj gate) same (control adj gate)) same (((bar (387) ((float\$3 adj gate) same (control adj gate)) and (((bar (1) ((float\$3 adj gate) same (control adj gate)) and (((bar (31) ((float\$3 adj gate) same (control adj gate)) and (ald (at (9) (((barrier adj height) (energy adj band))) near2 (asymme (41) (((float\$3 adj gate) same (control adj gate)) same (((bar (49) (((barrier adj height) (energy adj band))) near2 (asymme

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 (((barrier adj height) (energy adj band))) near2 (asymmet\$4 differen\$2) and ((float\$3 adj gate) and (control adj gate)) (((float\$3 adj gate) same (control adj gate)) same (((barrier near (height tunnel)) ((energy diagram) near band))) (work adj function))) and (metal adj oxide)) ((float\$3 adj gate) same (control adj gate)) and (ald (atomic adj layer adj deposit\$3)))

Dec 2022



U	Inventor	Document ID	Issue Date	Page	Title	Current OR	Current XRef	Ref
1	<input checked="" type="checkbox"/> Paraone, Lorenzo	US 4757360 A	19880712	6	Floating gate memory device with facing apertures on floating and control gates	257/317	257/900; 257/E29.304	
2	<input checked="" type="checkbox"/> Kan, Edwin C. et al.	US 20020192949 A1	20021219	14	Embedded metal nanocrystals	438/652	438/660	
3	<input checked="" type="checkbox"/> Lancaster, Loren T. et al.	US 5774400 A	19980630	14	Structure and method to prevent over erasure of nonvolatile memory transistors	365/185.3	365/185.18; 365/185.24	
4	<input checked="" type="checkbox"/> Lee, Jongho et al.	US 20020106536 A1	20020808	13	Dielectric layer for semiconductor device and method of manufacturing the same	428/702	428/428	
5	<input checked="" type="checkbox"/> Lee, Woo-Hyeong et al.	US 5923056 A	19990713	6	Electronic components with doped metal oxide dielectric materials and a process for making electronic components with doped metal oxide	257/192	257/410; 257/411	
6	<input checked="" type="checkbox"/> Muralidhar, Ramachandran et al.	US 6320784 B1	20011120	7	Memory cell and method for programming thereof	365/151	257/E29.301; 257/E29.308	
7	<input checked="" type="checkbox"/> Nguyen, Bich-Yen et al.	US 20020137250 A1	20020926	10	High K dielectric film and method for making	438/53		
8	<input checked="" type="checkbox"/> Uchida, Hidetsugu	US 6229175 B1	20010508	24	Nonvolatile memory	257/315	257/298; 257/316	

